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### What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I <sup>2</sup> C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	43
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 12x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21344cdfp-u0">https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21344cdfp-u0</a>

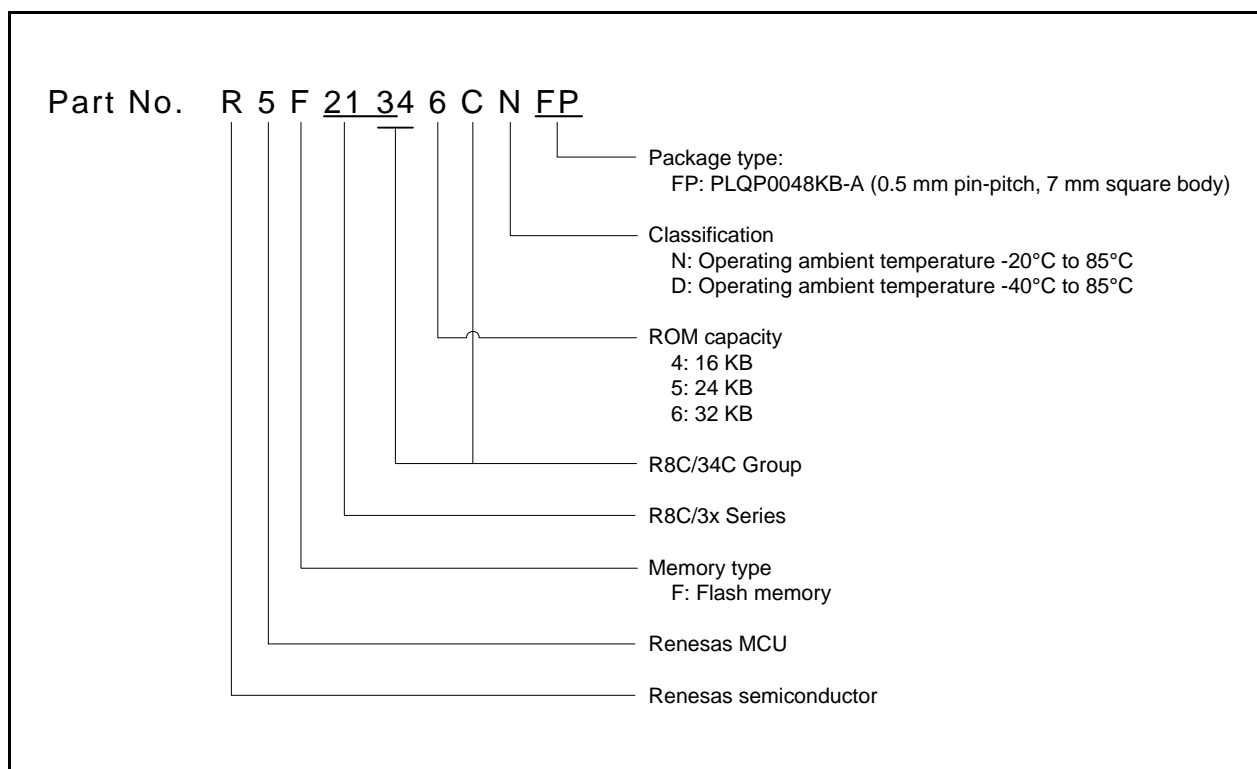
## 1.2 Product List

Table 1.3 lists Product List for R8C/34C Group, and Figure 1.1 shows a Part Number, Memory Size, and Package of R8C/34C Group.

**Table 1.3 Product List for R8C/34C Group**

**Current of Aug 2010**

Part No.	ROM Capacity		RAM Capacity	Package Type	Remarks
	Program ROM	Data flash			
R5F21344CNFP	16 Kbytes	1 Kbyte × 4	1.5 Kbytes	PLQP0048KB-A	N version
R5F21345CNFP	24 Kbytes	1 Kbyte × 4	2 Kbytes	PLQP0048KB-A	
R5F21346CNFP	32 Kbytes	1 Kbyte × 4	2.5 Kbytes	PLQP0048KB-A	
R5F21344CDFP	16 Kbytes	1 Kbyte × 4	1.5 Kbytes	PLQP0048KB-A	D version
R5F21345CDFP	24 Kbytes	1 Kbyte × 4	2 Kbytes	PLQP0048KB-A	
R5F21346CDFP	32 Kbytes	1 Kbyte × 4	2.5 Kbytes	PLQP0048KB-A	



**Figure 1.1 Part Number, Memory Size, and Package of R8C/34C Group**

**Table 1.4 Pin Name Information by Pin Number (1)**

Pin Number	Control Pin	Port	I/O Pin Functions for Peripheral Modules					
			Interrupt	Timer	Serial Interface	SSU	I <sup>2</sup> C bus	A/D Converter, D/A Converter, Comparator B
1		P6_0		(TREO)				
2		P3_0		(TRAO)				
3		P4_2						VREF
4	MODE							
5	(XCIN)	P4_3						
6	(XCOUT)	P4_4						
7	RESET							
8	XOUT	P4_7						
9	VSS/AVSS							
10	XIN	P4_6						
11	VCC/AVCC							
12		P3_7		TRAO	(RXD2/SCL2/ TXD2/SDA2)	SSO	SDA	
13		P3_5		(TRCIOD)	(CLK2)	SSCK	SCL	
14		P3_4		(TRCIOC)	(RXD2/SCL2/ TXD2/SDA2)	SSI		IVREF3
15		P3_3	$\overline{\text{INT3}}$	(TRCCLK)	( $\overline{\text{CTS2}}$ /RTS2)	$\overline{\text{SCS}}$		IVCMP3
16		P2_7		(TRDIOD1)				
17		P2_6		(TRDIOC1)				
18		P2_5		(TRDIOB1)				
19		P2_4		(TRDIOA1)				
20		P2_3		(TRDIOD0)				
21		P2_2		(TRCIOD/ TRDIOB0)				
22		P2_1		(TRCIOC/ TRDIOC0)				
23		P2_0	( $\overline{\text{INT1}}$ )	(TRCIOB/ TRDIOA0/ TRDCLK)				
24		P3_1		(TRBO)				
25		P6_7	( $\overline{\text{INT3}}$ )	(TRCIOD)				
26		P6_6	$\overline{\text{INT2}}$	(TRCIOC)	(TXD2/SDA2)			
27		P6_5	$\overline{\text{INT4}}$	(TRCIOB)	(CLK1/CLK2)			
28		P4_5	$\overline{\text{INT0}}$		(RXD2/SCL2)			$\overline{\text{ADTRG}}$
29		P1_7	$\overline{\text{INT1}}$	(TRAIO)				IVCMP1
30		P1_6			(CLK0)			IVREF1
31		P1_5	( $\overline{\text{INT1}}$ )	(TRAIO)	(RXD0)			
32		P1_4		(TRCCLK)	(TXD0)			
33		P1_3	$\overline{\text{KI3}}$	TRBO/ (TRCIOC)				AN11
34		P1_2	$\overline{\text{KI2}}$	(TRCIOB)				AN10
35		P1_1	$\overline{\text{KI1}}$	(TRCIOA/ TRCTR)				AN9

Note:

1. Can be assigned to the pin in parentheses by a program.

## 1.5 Pin Functions

Tables 1.6 and 1.7 list Pin Functions.

**Table 1.6 Pin Functions (1)**

Item	Pin Name	I/O Type	Description
Power supply input	VCC, VSS	–	Apply 1.8 V to 5.5 V to the VCC pin. Apply 0 V to the VSS pin.
Analog power supply input	AVCC, AVSS	–	Power supply for the A/D converter. Connect a capacitor between AVCC and AVSS.
Reset input	$\overline{\text{RESET}}$	I	Input “L” on this pin resets the MCU.
MODE	MODE	I	Connect this pin to VCC via a resistor.
XIN clock input	XIN	I	These pins are provided for XIN clock generation circuit I/O. Connect a ceramic resonator or a crystal oscillator between the XIN and XOUT pins <sup>(1)</sup> . To use an external clock, input it to the XOUT pin and leave the XIN pin open.
XIN clock output	XOUT	I/O	
XCIN clock input	XCIN	I	These pins are provided for XCIN clock generation circuit I/O. Connect a crystal oscillator between the XCIN and XCOUT pins <sup>(1)</sup> . To use an external clock, input it to the XCIN pin and leave the XCOUT pin open.
XCIN clock output	XCOUT	O	
$\overline{\text{INT}}$ interrupt input	$\overline{\text{INT0}}$ to $\overline{\text{INT4}}$	I	$\overline{\text{INT}}$ interrupt input pins. $\overline{\text{INT0}}$ is timer RB, RC and RD input pin.
Key input interrupt	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	Key input interrupt input pins
Timer RA	TRAIO	I/O	Timer RA I/O pin
	TRA0	O	Timer RA output pin
Timer RB	TRBO	O	Timer RB output pin
Timer RC	TRCLK	I	External clock input pin
	TRCTRG	I	External trigger input pin
	TRCIOA, TRCIOB, TRCIOC, TRCIOD	I/O	Timer RC I/O pins
Timer RD	TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1	I/O	Timer RD I/O pins
	TRDCLK	I	External clock input pin
Timer RE	TRE0	O	Divided clock output pin
Serial interface	CLK0, CLK1, CLK2	I/O	Transfer clock I/O pins
	RXD0, RXD1, RXD2	I	Serial data input pins
	TXD0, TXD1, TXD2	O	Serial data output pins
	$\overline{\text{CTS2}}$	I	Transmission control input pin
	$\overline{\text{RTS2}}$	O	Reception control output pin
	SCL2	I/O	I <sup>2</sup> C mode clock I/O pin
	SDA2	I/O	I <sup>2</sup> C mode data I/O pin
I <sup>2</sup> C bus	SCL	I/O	Clock I/O pin
	SDA	I/O	Data I/O pin
SSU	SSI	I/O	Data I/O pin
	$\overline{\text{SCS}}$	I/O	Chip-select signal I/O pin
	SSCK	I/O	Clock I/O pin
	SSO	I/O	Data I/O pin

I: Input      O: Output      I/O: Input and output

Note:

1. Refer to the oscillator manufacturer for oscillation characteristics.

**Table 1.7 Pin Functions (2)**

Item	Pin Name	I/O Type	Description
Reference voltage input	VREF	I	Reference voltage input pin to A/D converter and D/A converter
A/D converter	AN0 to AN11	I	Analog input pins to A/D converter
	ADTRG	I	A/D external trigger input pin
D/A converter	DA0, DA1	O	D/A converter output pins
Comparator B	IVCMP1, IVCMP3	I	Comparator B analog voltage input pins
	IVREF1, IVREF3	I	Comparator B reference voltage input pins
I/O port	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0, P3_1, P3_3 to P3_5, P3_7, P4_3 to P4_7, P6_0 to P6_7	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. All ports can be used as LED drive ports.
Input port	P4_2	I	Input-only port

I: Input      O: Output      I/O: Input and output

## 4. Special Function Registers (SFRs)

An SFR (special function register) is a control register for a peripheral function. Tables 4.1 to 4.12 list the special function registers. Table 4.13 lists the ID Code Areas and Option Function Select Area.

**Table 4.1 SFR Information (1) (1)**

Address	Register	Symbol	After Reset
0000h			
0001h			
0002h			
0003h			
0004h	Processor Mode Register 0	PM0	00h
0005h	Processor Mode Register 1	PM1	00h
0006h	System Clock Control Register 0	CM0	00101000b
0007h	System Clock Control Register 1	CM1	00100000b
0008h	Module Standby Control Register	MSTCR	00h
0009h	System Clock Control Register 3	CM3	00h
000Ah	Protect Register	PRCR	00h
000Bh	Reset Source Determination Register	RSTFR	0XXXXXXb (2)
000Ch	Oscillation Stop Detection Register	OCD	00000100b
000Dh	Watchdog Timer Reset Register	WDTR	XXh
000Eh	Watchdog Timer Start Register	WDTS	XXh
000Fh	Watchdog Timer Control Register	WDTC	00111111b
0010h			
0011h			
0012h			
0013h			
0014h			
0015h	High-Speed On-Chip Oscillator Control Register 7	FRA7	When shipping
0016h			
0017h			
0018h			
0019h			
001Ah			
001Bh			
001Ch	Count Source Protection Mode Register	CSPR	00h 10000000b (3)
001Dh			
001Eh			
001Fh			
0020h			
0021h			
0022h			
0023h	High-Speed On-Chip Oscillator Control Register 0	FRA0	00h
0024h	High-Speed On-Chip Oscillator Control Register 1	FRA1	When shipping
0025h	High-Speed On-Chip Oscillator Control Register 2	FRA2	00h
0026h	On-Chip Reference Voltage Control Register	OCVREFCR	00h
0027h			
0028h	Clock Prescaler Reset Flag	CPSRF	00h
0029h	High-Speed On-Chip Oscillator Control Register 4	FRA4	When shipping
002Ah	High-Speed On-Chip Oscillator Control Register 5	FRA5	When shipping
002Bh	High-Speed On-Chip Oscillator Control Register 6	FRA6	When shipping
002Ch			
002Dh			
002Eh			
002Fh	High-Speed On-Chip Oscillator Control Register 3	FRA3	When shipping
0030h	Voltage Monitor Circuit Control Register	CMPA	00h
0031h	Voltage Monitor Circuit Edge Select Register	VCAC	00h
0032h			
0033h	Voltage Detect Register 1	VCA1	00001000b
0034h	Voltage Detect Register 2	VCA2	00h (4) 00100000b (5)
0035h			
0036h	Voltage Detection 1 Level Select Register	VD1LS	00000111b
0037h			
0038h	Voltage Monitor 0 Circuit Control Register	VW0C	1100X010b (4) 1100X011b (5)
0039h	Voltage Monitor 1 Circuit Control Register	VW1C	10001010b

X: Undefined

Notes:

1. The blank areas are reserved and cannot be accessed by users.
2. The CWR bit in the RSTFR register is set to 0 after power-on and voltage monitor 0 reset. Hardware reset, software reset, or watchdog timer reset does not affect this bit.
3. The CSPROINI bit in the OFS register is set to 0.
4. The LVDAS bit in the OFS register is set to 1.
5. The LVDAS bit in the OFS register is set to 0.

**Table 4.10 SFR Information (10) (1)**

Address	Register	Symbol	After Reset
2C70h	DTC Control Data 6	DTCD6	XXh
2C71h			XXh
2C72h			XXh
2C73h			XXh
2C74h			XXh
2C75h			XXh
2C76h			XXh
2C77h			XXh
2C78h	DTC Control Data 7	DTCD7	XXh
2C79h			XXh
2C7Ah			XXh
2C7Bh			XXh
2C7Ch			XXh
2C7Dh			XXh
2C7Eh			XXh
2C7Fh			XXh
2C80h	DTC Control Data 8	DTCD8	XXh
2C81h			XXh
2C82h			XXh
2C83h			XXh
2C84h			XXh
2C85h			XXh
2C86h			XXh
2C87h			XXh
2C88h	DTC Control Data 9	DTCD9	XXh
2C89h			XXh
2C8Ah			XXh
2C8Bh			XXh
2C8Ch			XXh
2C8Dh			XXh
2C8Eh			XXh
2C8Fh			XXh
2C90h	DTC Control Data 10	DTCD10	XXh
2C91h			XXh
2C92h			XXh
2C93h			XXh
2C94h			XXh
2C95h			XXh
2C96h			XXh
2C97h			XXh
2C98h	DTC Control Data 11	DTCD11	XXh
2C99h			XXh
2C9Ah			XXh
2C9Bh			XXh
2C9Ch			XXh
2C9Dh			XXh
2C9Eh			XXh
2C9Fh			XXh
2CA0h	DTC Control Data 12	DTCD12	XXh
2CA1h			XXh
2CA2h			XXh
2CA3h			XXh
2CA4h			XXh
2CA5h			XXh
2CA6h			XXh
2CA7h			XXh
2CA8h	DTC Control Data 13	DTCD13	XXh
2CA9h			XXh
2CAAh			XXh
2CABh			XXh
2CACH			XXh
2CADh			XXh
2CAEh			XXh
2CAFh			XXh

X: Undefined

Note:

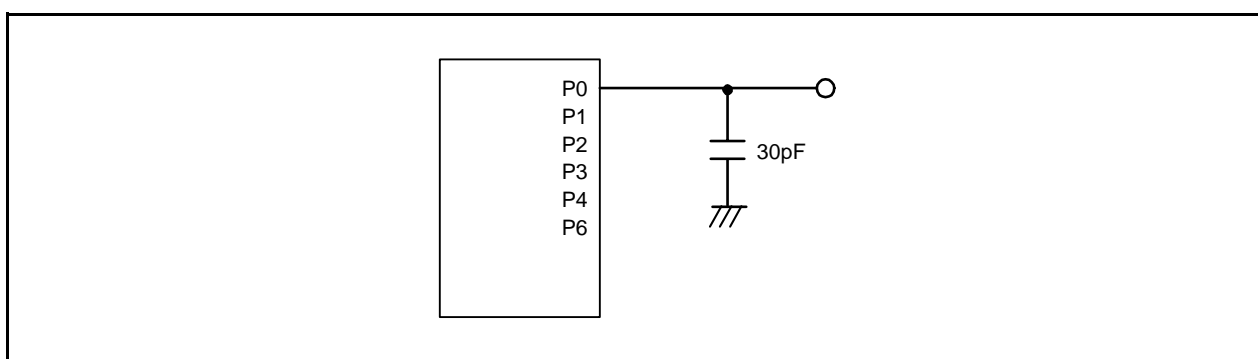
1. The blank areas are reserved and cannot be accessed by users.

**Table 5.2 Recommended Operating Conditions**

Symbol	Parameter				Conditions	Standard			Unit
						Min.	Typ.	Max.	
Vcc/AVcc	Supply voltage					1.8	–	5.5	V
Vss/AVss	Supply voltage					–	0	–	V
VIH	Input “H” voltage	Other than CMOS input				0.8 Vcc	–	Vcc	V
		CMOS input	Input level switching function (I/O port)	Input level selection : 0.35 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0.5 Vcc	–	Vcc	V
					2.7 V ≤ Vcc < 4.0 V	0.55 Vcc	–	Vcc	V
					1.8 V ≤ Vcc < 2.7 V	0.65 Vcc	–	Vcc	V
			Input level selection : 0.5 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0.65 Vcc	–	Vcc	V	
				2.7 V ≤ Vcc < 4.0 V	0.7 Vcc	–	Vcc	V	
				1.8 V ≤ Vcc < 2.7 V	0.8 Vcc	–	Vcc	V	
			Input level selection : 0.7 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0.85 Vcc	–	Vcc	V	
				2.7 V ≤ Vcc < 4.0 V	0.85 Vcc	–	Vcc	V	
				1.8 V ≤ Vcc < 2.7 V	0.85 Vcc	–	Vcc	V	
	External clock input (XOUT)				1.2	–	Vcc	V	
VIL	Input “L” voltage	Other than CMOS input				0	–	0.2 Vcc	V
		CMOS input	Input level switching function (I/O port)	Input level selection : 0.35 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0	–	0.2 Vcc	V
					2.7 V ≤ Vcc < 4.0 V	0	–	0.2 Vcc	V
					1.8 V ≤ Vcc < 2.7 V	0	–	0.2 Vcc	V
			Input level selection : 0.5 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0	–	0.4 Vcc	V	
				2.7 V ≤ Vcc < 4.0 V	0	–	0.3 Vcc	V	
				1.8 V ≤ Vcc < 2.7 V	0	–	0.2 Vcc	V	
			Input level selection : 0.7 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0	–	0.55 Vcc	V	
				2.7 V ≤ Vcc < 4.0 V	0	–	0.45 Vcc	V	
				1.8 V ≤ Vcc < 2.7 V	0	–	0.35 Vcc	V	
	External clock input (XOUT)				0	–	0.4	V	
IOH(sum)	Peak sum output “H” current	Sum of all pins IOH(peak)				–	–	–160	mA
IOH(sum)	Average sum output “H” current	Sum of all pins IOH(avg)				–	–	–80	mA
IOH(peak)	Peak output “H” current	Drive capacity Low				–	–	–10	mA
		Drive capacity High				–	–	–40	mA
IOH(avg)	Average output “H” current	Drive capacity Low				–	–	–5	mA
		Drive capacity High				–	–	–20	mA
IOL(sum)	Peak sum output “L” current	Sum of all pins IOL(peak)				–	–	160	mA
IOL(sum)	Average sum output “L” current	Sum of all pins IOL(avg)				–	–	80	mA
IOL(peak)	Peak output “L” current	Drive capacity Low				–	–	10	mA
		Drive capacity High				–	–	40	mA
IOL(avg)	Average output “L” current	Drive capacity Low				–	–	5	mA
		Drive capacity High				–	–	20	mA
f(XIN)	XIN clock input oscillation frequency				2.7 V ≤ Vcc ≤ 5.5 V	–	–	20	MHz
					1.8 V ≤ Vcc < 2.7 V	–	–	5	MHz
f(XCIN)	XCIN clock input oscillation frequency				1.8 V ≤ Vcc ≤ 5.5 V	–	32.768	50	kHz
fOCO40M	When used as the count source for timer RC or timer RD <sup>(3)</sup>				2.7 V ≤ Vcc ≤ 5.5 V	32	–	40	MHz
fOCO-F	fOCO-F frequency				2.7 V ≤ Vcc ≤ 5.5 V	–	–	20	MHz
					1.8 V ≤ Vcc < 2.7 V	–	–	5	MHz
–	System clock frequency				2.7 V ≤ Vcc ≤ 5.5 V	–	–	20	MHz
					1.8 V ≤ Vcc < 2.7 V	–	–	5	MHz
f(BCLK)	CPU clock frequency				2.7 V ≤ Vcc ≤ 5.5 V	–	–	20	MHz
					1.8 V ≤ Vcc < 2.7 V	–	–	5	MHz

## Notes:

1. V<sub>CC</sub> = 1.8 to 5.5 V and T<sub>opr</sub> = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.
3. f<sub>OCO40M</sub> can be used as the count source for timer RC or timer RD in the range of V<sub>CC</sub> = 2.7 V to 5.5V.



**Figure 5.1** Ports P0 to P4, P6 Timing Measurement Circuit

**Table 5.6 Flash Memory (Program ROM) Electrical Characteristics**

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance <sup>(2)</sup>		1,000 <sup>(3)</sup>	—	—	times
—	Byte program time		—	80	500	μs
—	Block erase time		—	0.3	—	s
t <sub>d</sub> (SR-SUS)	Time delay from suspend request until suspend		—	—	5+CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	μs
—	Time from suspend until erase restart		—	—	30+CPU clock × 1 cycle	μs
t <sub>d</sub> (CMDRST-READY)	Time from when command is forcibly stopped until reading is enabled		—	—	30+CPU clock × 1 cycle	μs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		0	—	60	°C
—	Data hold time <sup>(7)</sup>	Ambient temperature = 55°C	20	—	—	year

**Notes:**

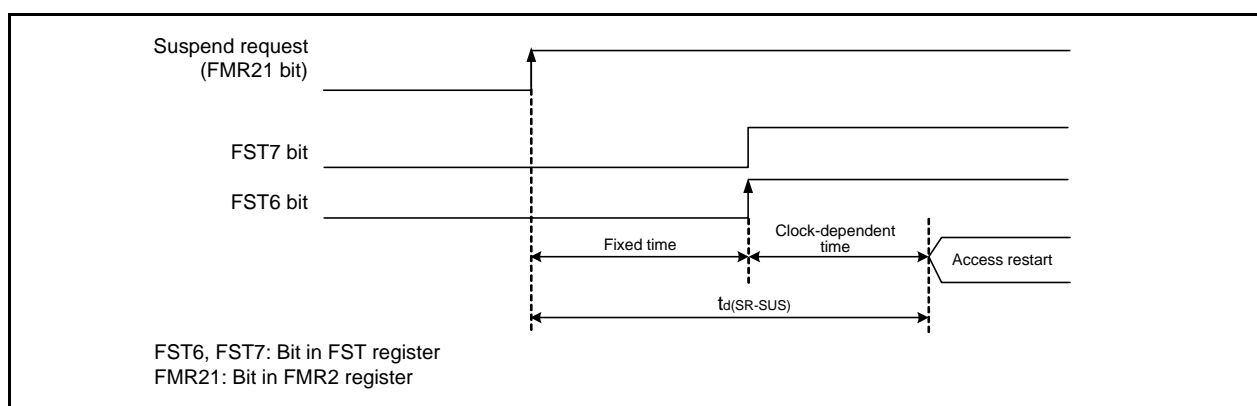
1. V<sub>CC</sub> = 2.7 to 5.5 V and T<sub>opr</sub> = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance  
The programming and erasure endurance is defined on a per-block basis.  
If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.  
However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

**Table 5.7 Flash Memory (Data flash Block A to Block D) Electrical Characteristics**

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance <sup>(2)</sup>		10,000 <sup>(3)</sup>	—	—	times
—	Byte program time (program/erase endurance ≤ 1,000 times)		—	160	1,500	μs
—	Byte program time (program/erase endurance > 1,000 times)		—	300	1,500	μs
—	Block erase time (program/erase endurance ≤ 1,000 times)		—	0.2	1	s
—	Block erase time (program/erase endurance > 1,000 times)		—	0.3	1	s
t <sub>d</sub> (SR-SUS)	Time delay from suspend request until suspend		—	—	5+CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	μs
—	Time from suspend until erase restart		—	—	30+CPU clock × 1 cycle	μs
t <sub>d</sub> (CMDRST-READY)	Time from when command is forcibly stopped until reading is enabled		—	—	30+CPU clock × 1 cycle	μs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		−20 <sup>(7)</sup>	—	85	°C
—	Data hold time <sup>(8)</sup>	Ambient temperature = 55 °C	20	—	—	year

**Notes:**

1. V<sub>CC</sub> = 2.7 to 5.5 V and T<sub>opr</sub> = −20 to 85°C (N version) / −40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance  
The programming and erasure endurance is defined on a per-block basis.  
If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.  
However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A to D can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. −40°C for D version.
8. The data hold time includes time that the power supply is off or the clock is not supplied.

**Figure 5.2 Time delay until Suspend**

**Table 5.12 High-speed On-Chip Oscillator Circuit Electrical Characteristics**

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
–	High-speed on-chip oscillator frequency after reset	$V_{CC} = 1.8\text{ V to }5.5\text{ V}$ $-20^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	38.4	40	41.6	MHz
		$V_{CC} = 1.8\text{ V to }5.5\text{ V}$ $-40^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	38.0	40	42.0	MHz
	High-speed on-chip oscillator frequency when the FRA4 register correction value is written into the FRA1 register and the FRA5 register correction value into the FRA3 register <sup>(2)</sup>	$V_{CC} = 1.8\text{ V to }5.5\text{ V}$ $-20^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	35.389	36.864	38.338	MHz
		$V_{CC} = 1.8\text{ V to }5.5\text{ V}$ $-40^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	35.020	36.864	38.707	MHz
	High-speed on-chip oscillator frequency when the FRA6 register correction value is written into the FRA1 register and the FRA7 register correction value into the FRA3 register	$V_{CC} = 1.8\text{ V to }5.5\text{ V}$ $-20^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	30.72	32	33.28	MHz
		$V_{CC} = 1.8\text{ V to }5.5\text{ V}$ $-40^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	30.40	32	33.60	MHz
–	Oscillation stability time	$V_{CC} = 5.0\text{ V}$ , $T_{opr} = 25^{\circ}\text{C}$	–	0.5	3	ms
–	Self power consumption at oscillation	$V_{CC} = 5.0\text{ V}$ , $T_{opr} = 25^{\circ}\text{C}$	–	400	–	$\mu\text{A}$

Notes:

1.  $V_{CC} = 1.8$  to  $5.5\text{ V}$ ,  $T_{opr} = -20$  to  $85^{\circ}\text{C}$  (N version) /  $-40$  to  $85^{\circ}\text{C}$  (D version), unless otherwise specified.
2. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

**Table 5.13 Low-speed On-Chip Oscillator Circuit Electrical Characteristics**

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		60	125	250	kHz
–	Oscillation stability time	$V_{CC} = 5.0\text{ V}$ , $T_{opr} = 25^{\circ}\text{C}$	–	30	100	$\mu\text{s}$
–	Self power consumption at oscillation	$V_{CC} = 5.0\text{ V}$ , $T_{opr} = 25^{\circ}\text{C}$	–	2	–	$\mu\text{A}$

Note:

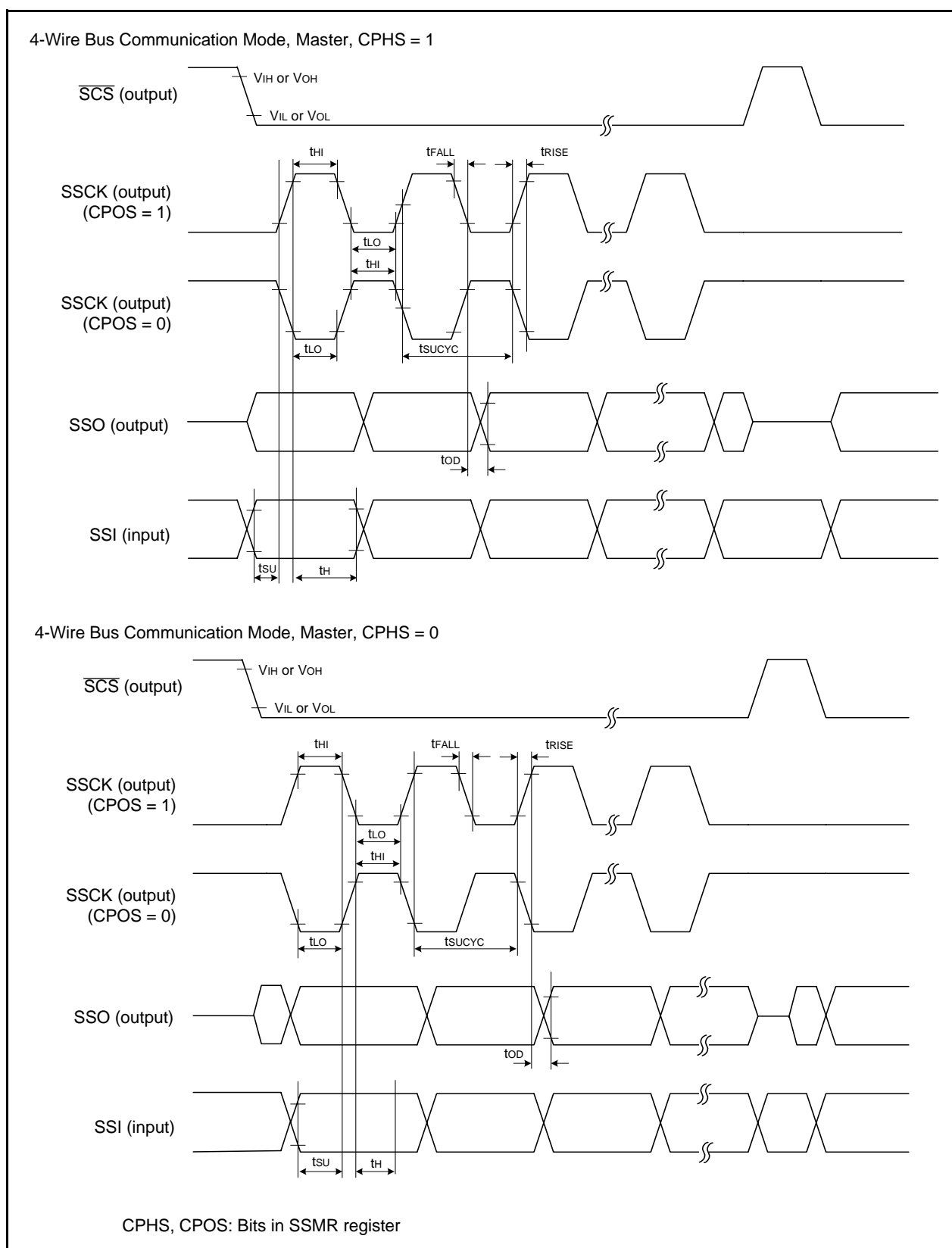
1.  $V_{CC} = 1.8$  to  $5.5\text{ V}$ ,  $T_{opr} = -20$  to  $85^{\circ}\text{C}$  (N version) /  $-40$  to  $85^{\circ}\text{C}$  (D version), unless otherwise specified.

**Table 5.14 Power Supply Circuit Timing Characteristics**

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t <sub>d</sub> (P-R)	Time for internal power supply stabilization during power-on <sup>(2)</sup>		–	–	2,000	$\mu\text{s}$

Notes:

1. The measurement condition is  $V_{CC} = 1.8$  to  $5.5\text{ V}$  and  $T_{opr} = 25^{\circ}\text{C}$ .
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.



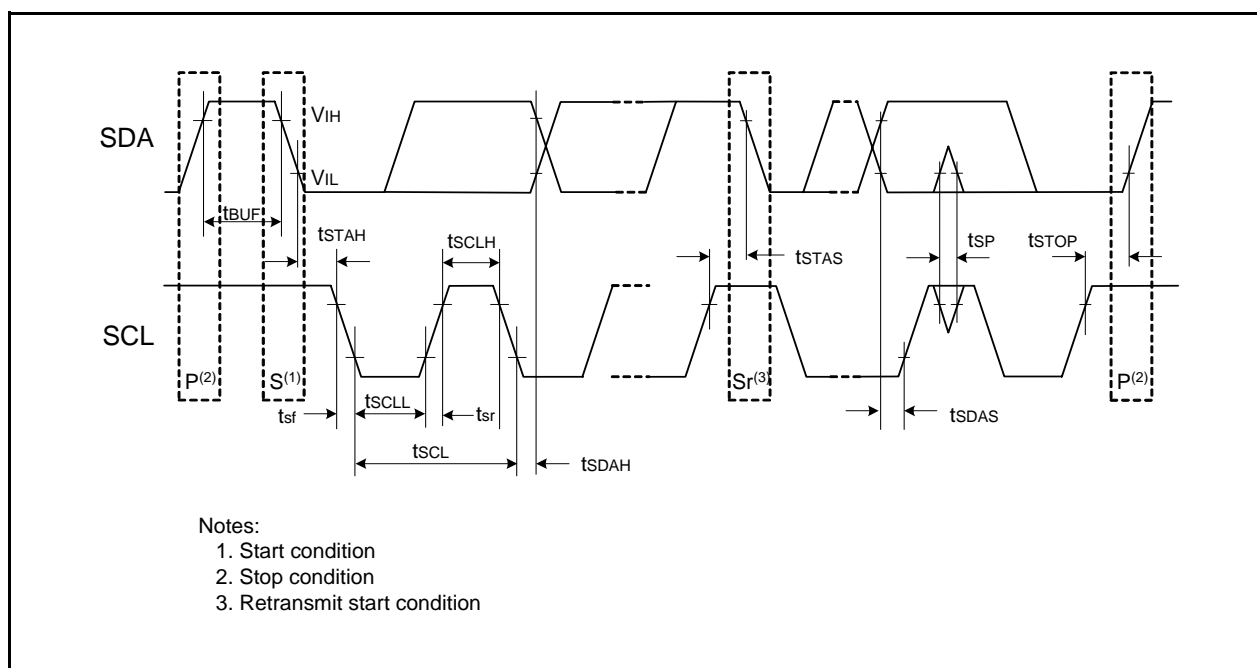
**Figure 5.4 I/O Timing of Synchronous Serial Communication Unit (SSU) (Master)**

**Table 5.16 Timing Requirements of I<sup>2</sup>C bus Interface (1)**

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
tSCL	SCL input cycle time		12tcyc + 600 (2)	—	—	ns
tSCLH	SCL input "H" width		3tcyc + 300 (2)	—	—	ns
tSCLL	SCL input "L" width		5tcyc + 500 (2)	—	—	ns
tsf	SCL, SDA input fall time		—	—	300	ns
tSP	SCL, SDA input spike pulse rejection time		—	—	1tcyc (2)	ns
tBUF	SDA input bus-free time		5tcyc (2)	—	—	ns
tSTAH	Start condition input hold time		3tcyc (2)	—	—	ns
tSTAS	Retransmit start condition input setup time		3tcyc (2)	—	—	ns
tSTOP	Stop condition input setup time		3tcyc (2)	—	—	ns
tSDAS	Data input setup time		1tcyc + 40 (2)	—	—	ns
tSDAH	Data input hold time		10	—	—	ns

Notes:

1. VCC = 1.8 to 5.5 V, VSS = 0 V and T<sub>opr</sub> = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. 1tcyc = 1/f1(s)

**Figure 5.7 I/O Timing of I<sup>2</sup>C bus Interface**

**Table 5.23 Electrical Characteristics (3) [2.7 V ≤ Vcc < 4.2 V]**

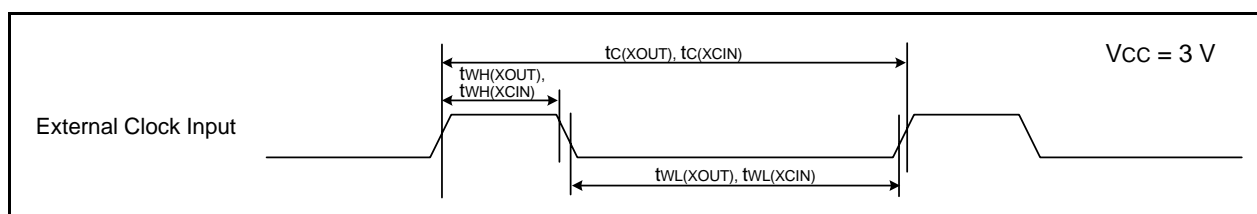
Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
VOH	Output "H" voltage	Other than XOUT	Drive capacity High	IOH = −5 mA	Vcc − 0.5	−	Vcc	V
			Drive capacity Low	IOH = −1 mA	Vcc − 0.5	−	Vcc	V
		XOUT		IOH = −200 μA	1.0	−	Vcc	V
VOL	Output "L" voltage	Other than XOUT	Drive capacity High	IOL = 5 mA	−	−	0.5	V
			Drive capacity Low	IOL = 1 mA	−	−	0.5	V
		XOUT		IOL = 200 μA	−	−	0.5	V
VT+ - VT-	Hysteresis	INT0, INT1, INT2, INT3, INT4, KI0, KI1, KI2, KI3, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRDIOA0, TRDIOB0, TRDIOC0, TRDIOD0, TRDIOA1, TRDIOB1, TRDIOC1, TRDIOD1, TRCTRG, TRCCLK, ADTRG, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO	Vcc = 3.0 V		0.1	0.4	−	V
		RESET	Vcc = 3.0 V		0.1	0.5	−	V
IiH	Input "H" current		VI = 3 V, Vcc = 3.0 V		−	−	4.0	μA
IiL	Input "L" current		VI = 0 V, Vcc = 3.0 V		−	−	−4.0	μA
RPULLUP	Pull-up resistance		VI = 0 V, Vcc = 3.0 V		42	84	168	kΩ
RiXIN	Feedback resistance	XIN			−	0.3	−	MΩ
RiXCIN	Feedback resistance	XCIN			−	8	−	MΩ
VRAM	RAM hold voltage		During stop mode		1.8	−	−	V

Note:

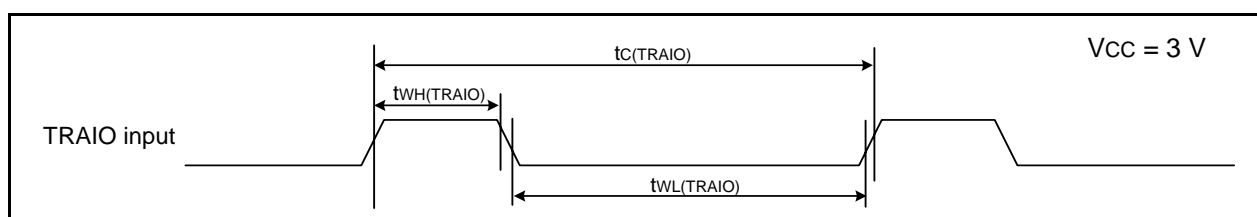
- 2.7 V ≤ Vcc < 4.2 V at Topr = −20 to 85°C (N version) / −40 to 85°C (D version), f(XIN) = 10 MHz, unless otherwise specified.

**Timing Requirements****(Unless Otherwise Specified:  $V_{CC} = 3\text{ V}$ ,  $V_{SS} = 0\text{ V}$  at  $T_{op} = 25^{\circ}\text{C}$ )****Table 5.25 External Clock Input (XOUT, XCIN)**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XOUT)}$	XOUT input cycle time	50	–	ns
$t_{WH(XOUT)}$	XOUT input “H” width	24	–	ns
$t_{WL(XOUT)}$	XOUT input “L” width	24	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	–	$\mu\text{s}$
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	$\mu\text{s}$
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	$\mu\text{s}$

**Figure 5.12 External Clock Input Timing Diagram when  $V_{CC} = 3\text{ V}$** **Table 5.26 TRAIO Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	300	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	120	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	120	–	ns

**Figure 5.13 TRAIO Input Timing Diagram when  $V_{CC} = 3\text{ V}$**

**Table 5.29 Electrical Characteristics (5) [ $1.8\text{ V} \leq V_{CC} < 2.7\text{ V}$ ]**

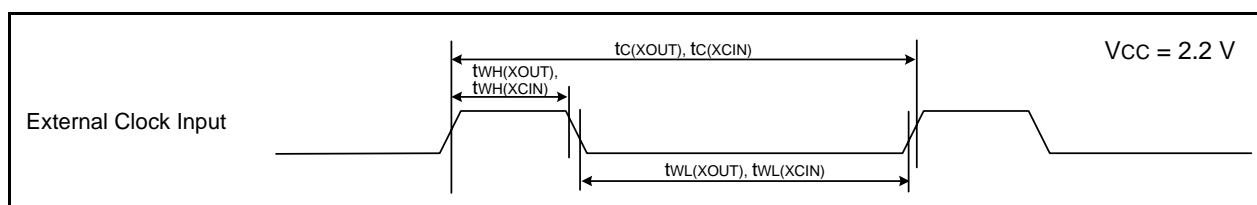
Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V <sub>OH</sub>	Output "H" voltage	Other than XOUT	Drive capacity High	I <sub>OH</sub> = -2 mA	V <sub>CC</sub> - 0.5	—	V <sub>CC</sub>	V
			Drive capacity Low	I <sub>OH</sub> = -1 mA	V <sub>CC</sub> - 0.5	—	V <sub>CC</sub>	V
		XOUT		I <sub>OH</sub> = -200 $\mu$ A	1.0	—	V <sub>CC</sub>	V
V <sub>OL</sub>	Output "L" voltage	Other than XOUT	Drive capacity High	I <sub>OL</sub> = 2 mA	—	—	0.5	V
			Drive capacity Low	I <sub>OL</sub> = 1 mA	—	—	0.5	V
		XOUT		I <sub>OL</sub> = 200 $\mu$ A	—	—	0.5	V
V <sub>T+</sub> -V <sub>T-</sub>	Hysteresis	INT0, INT1, INT2, INT3, INT4, KI0, KI1, KI2, KI3, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRDIOA0, TRDIOB0, TRDIOC0, TRDIOD0, TRDIOA1, TRDIOB1, TRDIOC1, TRDIOD1, TRCTRG, TRCCLK, ADTRG, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO			0.05	0.2	—	V
		RESET			0.05	0.20	—	V
I <sub>IH</sub>	Input "H" current		V <sub>I</sub> = 2.2 V, V <sub>CC</sub> = 2.2 V		—	—	4.0	$\mu$ A
I <sub>IL</sub>	Input "L" current		V <sub>I</sub> = 0 V, V <sub>CC</sub> = 2.2 V		—	—	-4.0	$\mu$ A
R <sub>PULLUP</sub>	Pull-up resistance		V <sub>I</sub> = 0 V, V <sub>CC</sub> = 2.2 V		70	140	300	k $\Omega$
R <sub>FXIN</sub>	Feedback resistance	XIN			—	0.3	—	M $\Omega$
R <sub>FXCIN</sub>	Feedback resistance	XCIN			—	8	—	M $\Omega$
V <sub>RAM</sub>	RAM hold voltage		During stop mode		1.8	—	—	V

Note:

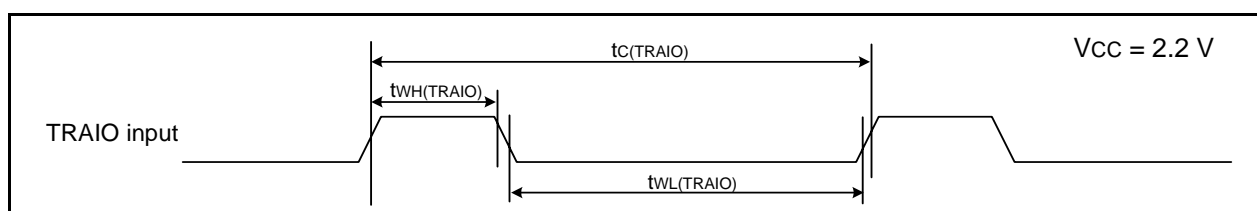
1.  $1.8\text{ V} \leq V_{CC} < 2.7\text{ V}$ , T<sub>opr</sub> = -20 to 85°C (N version) / -40 to 85°C (D version), f(XIN) = 5 MHz, unless otherwise specified.

**Timing Requirements****(Unless Otherwise Specified:  $V_{CC} = 2.2\text{ V}$ ,  $V_{SS} = 0\text{ V}$  at  $T_{opr} = 25^{\circ}\text{C}$ )****Table 5.31 External Clock Input (XOUT, XCIN)**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_c(\text{XOUT})$	XOUT input cycle time	200	–	ns
$t_{WH}(\text{XOUT})$	XOUT input “H” width	90	–	ns
$t_{WL}(\text{XOUT})$	XOUT input “L” width	90	–	ns
$t_c(\text{XCIN})$	XCIN input cycle time	14	–	$\mu\text{s}$
$t_{WH}(\text{XCIN})$	XCIN input “H” width	7	–	$\mu\text{s}$
$t_{WL}(\text{XCIN})$	XCIN input “L” width	7	–	$\mu\text{s}$

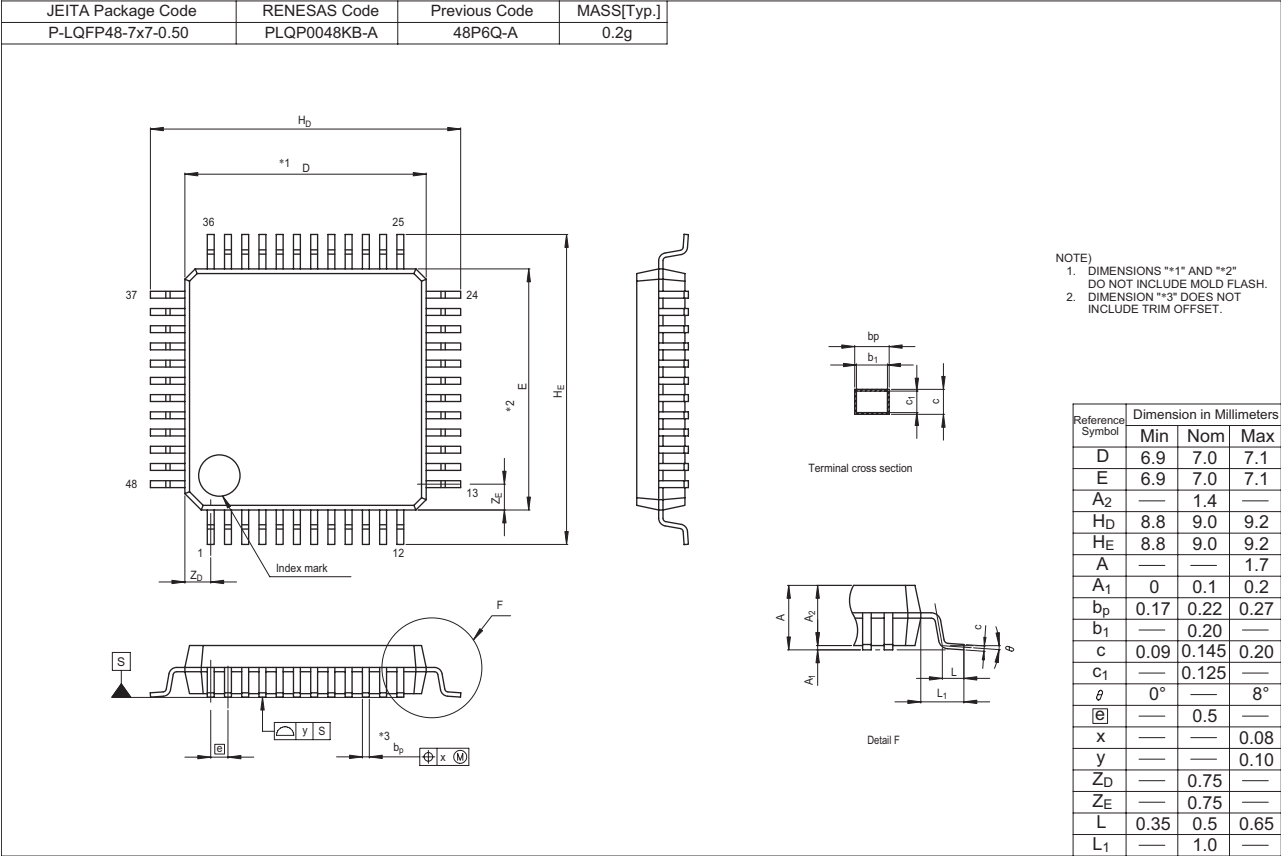
**Figure 5.16 External Clock Input Timing Diagram when  $V_{CC} = 2.2\text{ V}$** **Table 5.32 TRAIO Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_c(\text{TRAIO})$	TRAIO input cycle time	500	–	ns
$t_{WH}(\text{TRAIO})$	TRAIO input “H” width	200	–	ns
$t_{WL}(\text{TRAIO})$	TRAIO input “L” width	200	–	ns

**Figure 5.17 TRAIO Input Timing Diagram when  $V_{CC} = 2.2\text{ V}$**

Package Dimensions

Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Electronics website.



## General Precautions in the Handling of MPU/MCU Products

The following usage notes are applicable to all MPU/MCU products from Renesas. For detailed usage notes on the products covered by this manual, refer to the relevant sections of the manual. If the descriptions under General Precautions in the Handling of MPU/MCU Products and in the body of the manual differ from each other, the description in the body of the manual takes precedence.

### 1. Handling of Unused Pins

Handle unused pins in accord with the directions given under Handling of Unused Pins in the manual.

- The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible. Unused pins should be handled as described under Handling of Unused Pins in the manual.

### 2. Processing at Power-on

The state of the product is undefined at the moment when power is supplied.

- The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the moment when power is supplied.

In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the moment when power is supplied until the reset process is completed.

In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the moment when power is supplied until the power reaches the level at which resetting has been specified.

### 3. Prohibition of Access to Reserved Addresses

Access to reserved addresses is prohibited.

- The reserved addresses are provided for the possible future expansion of functions. Do not access these addresses; the correct operation of LSI is not guaranteed if they are accessed.

### 4. Clock Signals

After applying a reset, only release the reset line after the operating clock signal has become stable. When switching the clock signal during program execution, wait until the target clock signal has stabilized.

- When the clock signal is generated with an external resonator (or from an external oscillator) during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Moreover, when switching to a clock signal produced with an external resonator (or by an external oscillator) while program execution is in progress, wait until the target clock signal is stable.

### 5. Differences between Products

Before changing from one product to another, i.e. to one with a different part number, confirm that the change will not lead to problems.

- The characteristics of MPU/MCU in the same group but having different part numbers may differ because of the differences in internal memory capacity and layout pattern. When changing to products of different part numbers, implement a system-evaluation test for each of the products.

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